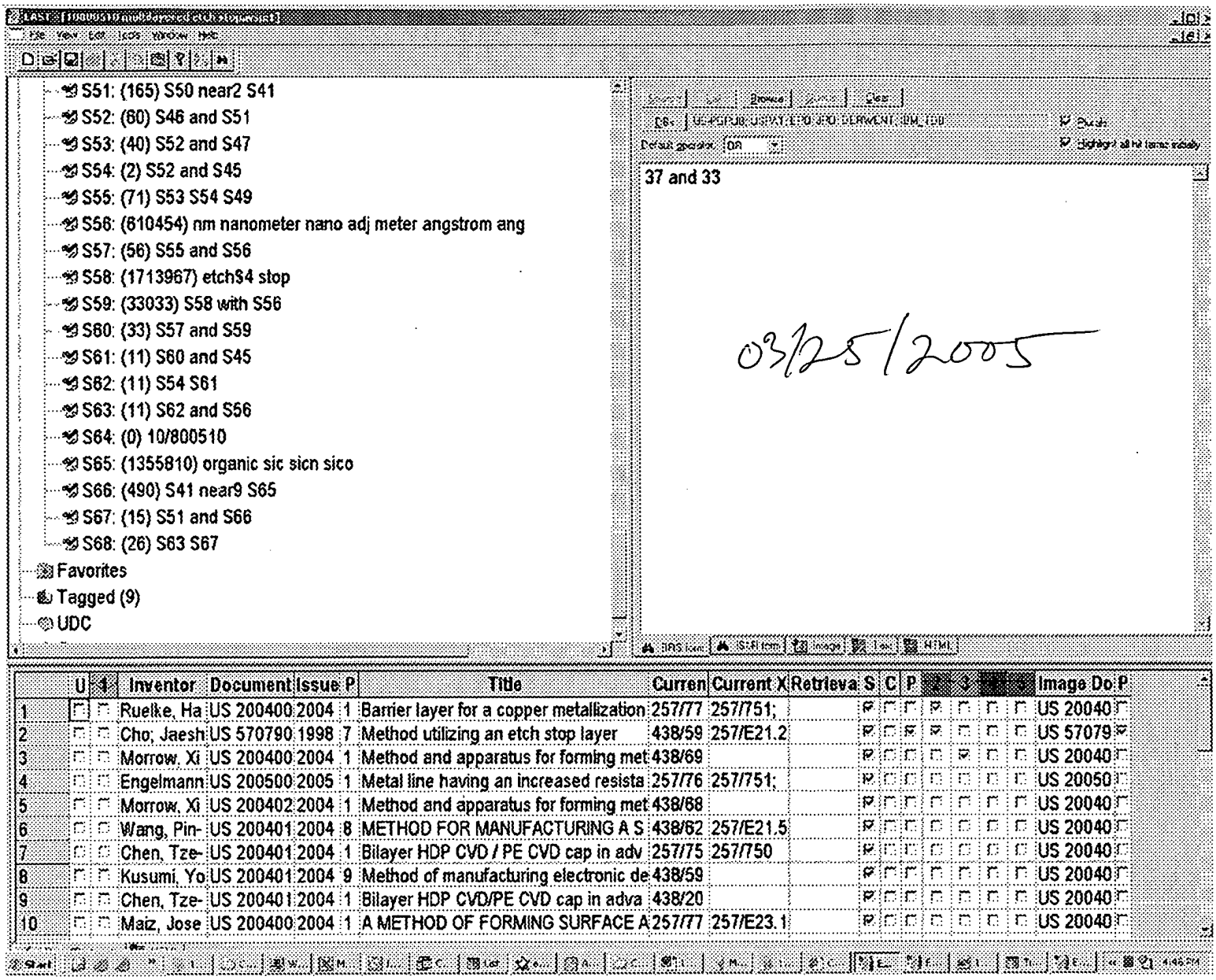
S51: (165) S50 near2 S41
S52: (60) S46 and S51
S53: (40) S52 and S47
S54: (2) S52 and S45
S55: (71) S53 S54 S49
S56: (810454) nm nanometer nano adj meter angstrom ang
S57: (56) S55 and S56
S58: (1713967) etch$4 stop
S59: (33033) S58 with S56
S60: (33) S57 and S59
S61: (11) S60 and S45
S62: (11) S54 S61
S63: (11) S62 and S56
S64: (0) 10/800510
S65: (1355810) organic sic sicn sico
S66: (490) S41 near9 S65
S67: (15) S51 and S66
S68: (26) S63 S67
Favorites
Tagged (9)
UDC
37 and 33
03/25/2005
U
1
Inventor
Document
Issue
P
Title
Curren
Current X
Retrieva
S
C
P
Image Do
P
1 Ruelke, Ha US 200400 2004 1 Barrier layer for a copper metallization 257/77 257/751; US 20040
2 Cho; Jaesh US 570790 1998 7 Method utilizing an etch stop layer 438/59 257/E21.2 US 57079
3 Morrow, Xi US 200400 2004 1 Method and apparatus for forming met 438/69 US 20040
4 Engelmann US 200500 2005 1 Metal line having an increased resista 257/76 257/751; US 20050
5 Morrow, Xi US 200402 2004 1 Method and apparatus for forming met 438/68 US 20040
6 Wang, Pin- US 200401 2004 8 METHOD FOR MANUFACTURING A S 438/62 257/E21.5 US 20040
7 Chen, Tze- US 200401 2004 1 Bilayer HDP CVD / PE CVD cap in adv 257/75 257/750 US 20040
8 Kusumi, Yo US 200401 2004 9 Method of manufacturing electronic de 438/59 US 20040
9 Chen, Tze- US 200401 2004 1 Bilayer HDP CVD/PE CVD cap in adva 438/20 US 20040
10 Maiz, Jose US 200400 2004 1 A METHOD OF FORMING SURFACE A 257/77 257/E23.1 US 20040